alpha pacific

DEVICE SPECIFICATION

APQ12SN60AH
APQ12SN60AF

600V/12A N-Channel MOSFET

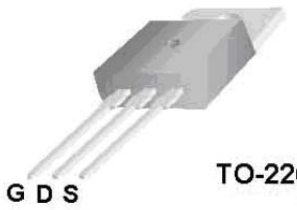
1 Description

These N-Channel enhancement mode power field effect transistors are produced using planar stripe, DMOS technology.

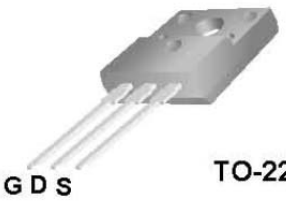
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

2 Features

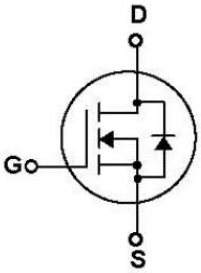
- 600V / 12A
- $R_{DS(on)}$ = 0.52Ω(typ)，V_{GS} = 10 V ,I_D =7.2A
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability..



TO-220



TO-220F



3 Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	APQ12SN60AH-XXM0 APQ12SN60AH-XXJ0 TO-220	APQ12SN60AF-XXM0 APQ12SN60AF-XXJ0 TO-220F	Units
V_{DSS}	Drain-Source Voltage	600		V
I_D	Drain Current - Continuous (T_C= 25°C)	12		A
	- Continuous (T_C= 100°C)	7.2		A
I_{DM}	Drain Current - Pulsed ①	48		A
V_{GS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy ②	870		mJ
I_{AR}	Avalanche Current ①	12		A
E_{AR}	Repetitive Avalanche Energy ①	22.5		mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5		V/ns
P_D	Power Dissipation (T_C= 25°C)	225	51	W
	- De-ate above 25°C	1.78	0.41	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		°C

* note :

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② V_{DD}=50V, starting T_J=25℃, L=TBD, R_G=25Ω, I_{AS}=12A

③ I_{SD} ≤ 12A, di/dt ≤ 100A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150℃.

4 Thermal Characteristics

Symbol	Parameter	APQ12SN60AH-XXM0 APQ12SN60AH-XXJ0 TO-220	APQ12SN60AF-XXM0 APQ12SN60AF-XXJ0 TO-220F	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.56	2.43	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

5 Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}= 0 V, I_D= 250 μA	600	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D= 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I_{DSS}	Gate to Source leakage current	V_{DS}= 600 V, V_{GS} = 0 V	--	--	20	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS}= 30 V, V_{DS}= 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS}= -30 V, V_{DS}= 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= 250 μA ④	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS}= 10 V, I_D= 7.2 A	--	0.52	0.65	Ω
g_{FS}	Forward Transconductance	V_{DS}= 15 V, I_D = 6A ④	--	--	20	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= 25 V, V_{GS}= 0 V, f = 1.0 MHz	--	1755	--	pF
C_{oss}	Output Capacitance		--	180	--	pF
C_{rss}	Reverse Transfer Capacitance		--	20	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}= 300 V, I_D= 12A, R_G= 25Ω ④	--	31	-	ns
t_r	Turn-On Rise Time		--	83	-	ns
$t_{d(off)}$	Turn-Off Delay Time		--	135	-	ns
t_f	Turn-Off Fall Time		--	92	-	ns
Q_g	Total Gate Charge	V_{DS}= 300 V, I_D= 12A, V_{GS}= 10 V ④	--	50		nC
Q_{gs}	Gate-Source Charge		--	8.7		nC
Q_{gd}	Gate-Drain Charge		--	20		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48	A

V_{SD}	Drain-Source Diode Forward Voltage	V_{GS}= 0 V, I_S= 6 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V, I_S= 12 A, di / dt = 100 A/μs ④	--	420	--	ns
Q_{rr}	Reverse Recovery Charge		--	5.0	--	μC

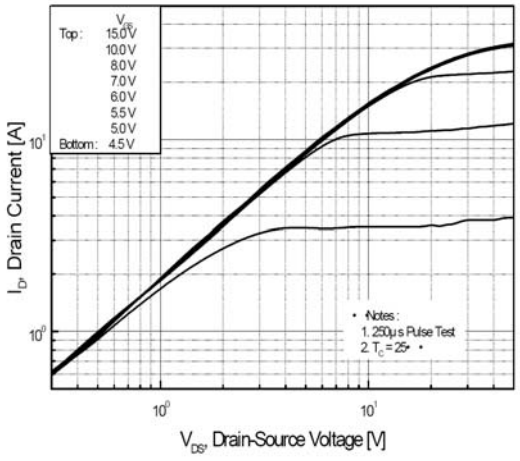
Notes:

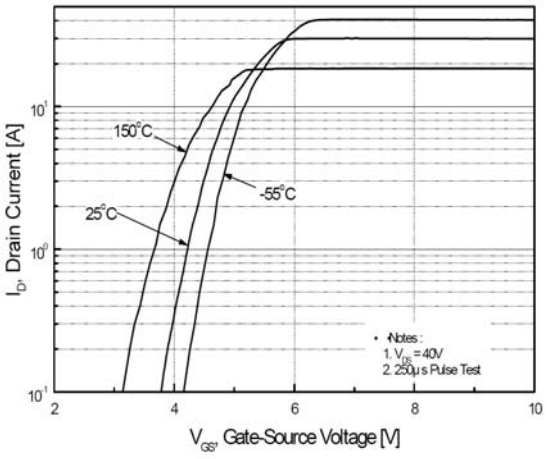
① Repetitive Rating: Pulse width limited by maximum junction temperature.

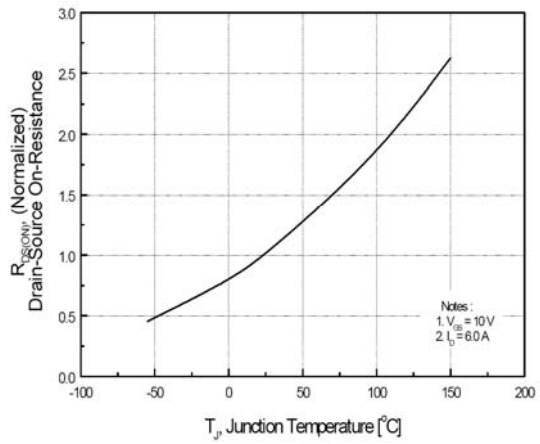
② V_{DD}=50V, starting TJ=25℃, L=TBD, RG=25Ω, I_{AS}=12A

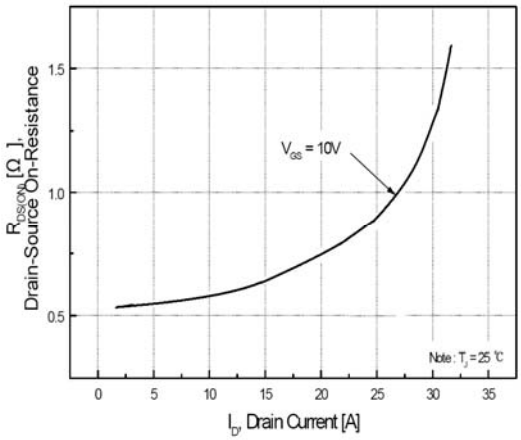
③ I_{SD} ≤ 12A, di/dt ≤ 100A/μs, VDD ≤ V(BR)DSS, TJ ≤ 150℃

④ Pulse Test: Pulse width ≤300μs, Duty cycle ≤ 2%. Depend on FT Test.









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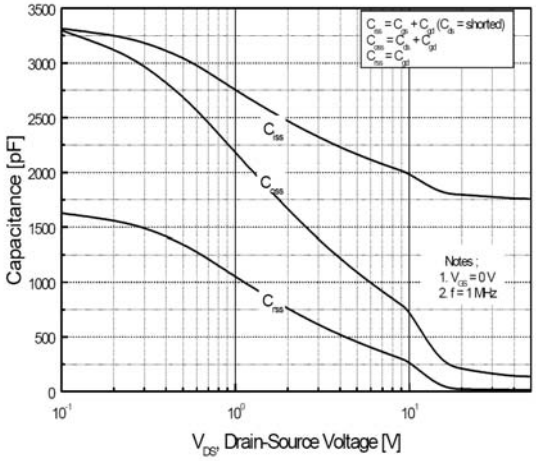
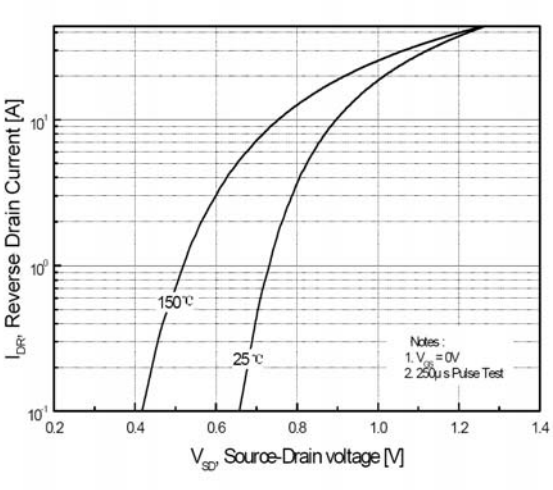
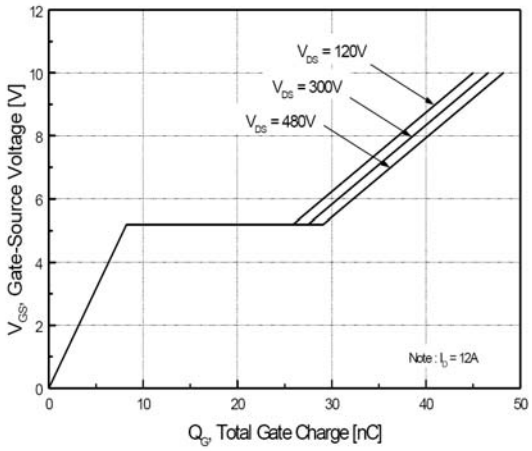
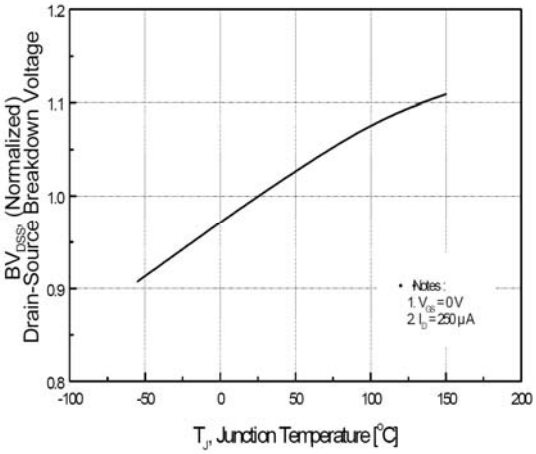
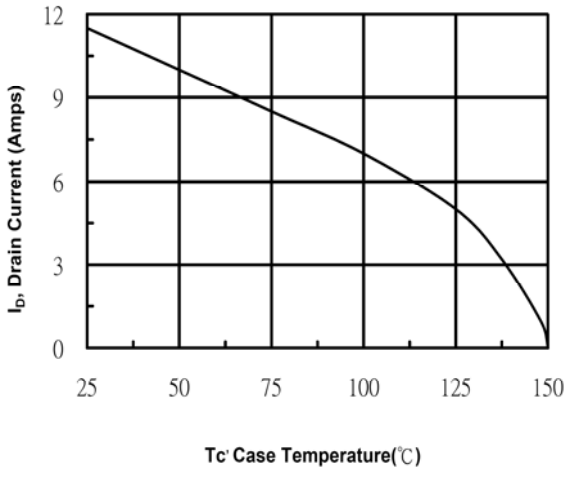


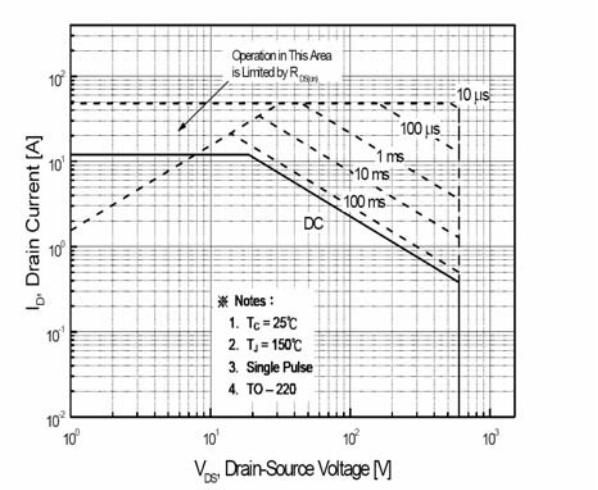


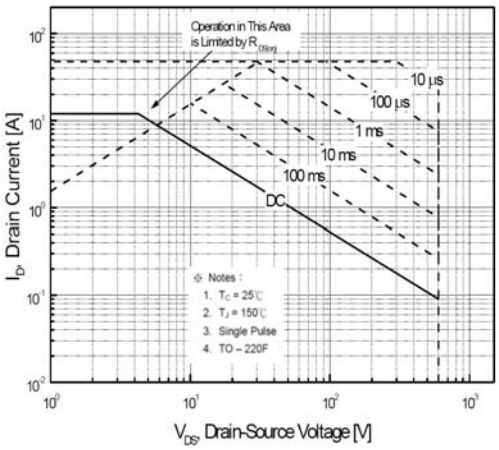


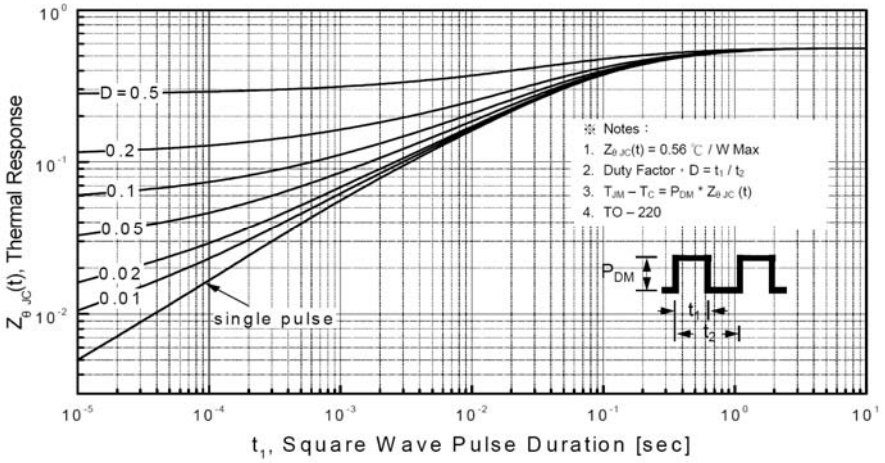


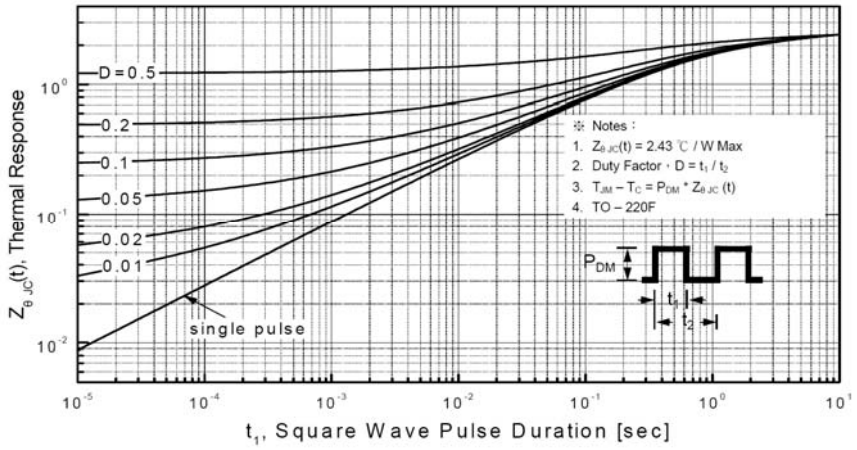


600V/12A N-Channel MOSFET





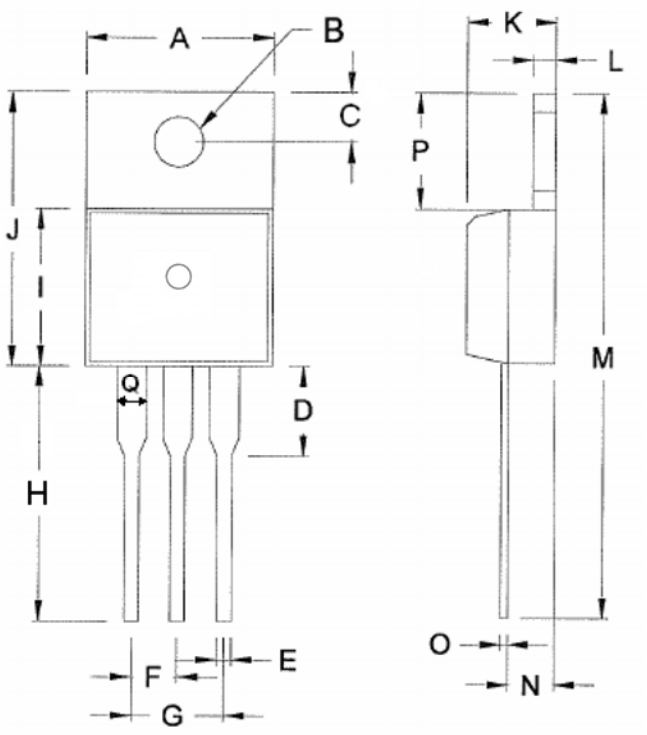




6 Package Dimensions

APQ12SN60AH-XXM0
TO-220

TO-220 DIMENSION			
DIM	MILLIMETERS		
	MIN	MAX	TYP.
A	10.04	10.41	10.23
B	3.66	3.88	3.77
C	2.50	2.84	2.67
D	3.31	4.50	3.91
E	0.70	0.91	0.81
F	2.54(typ.)		2.54
G	5.08(typ.)		5.08
H	13.47	14.20	13.84
I	8.50	9.00	8.80
J	14.80	15.49	15.15
K	4.32	4.57	4.45
L	1.22	1.42	1.30
M	28.27	29.69	28.98
N	2.40	2.90	2.65
O	0.36	0.53	0.45
P	5.97	6.47	6.22
Q	1.15	1.45	1.30



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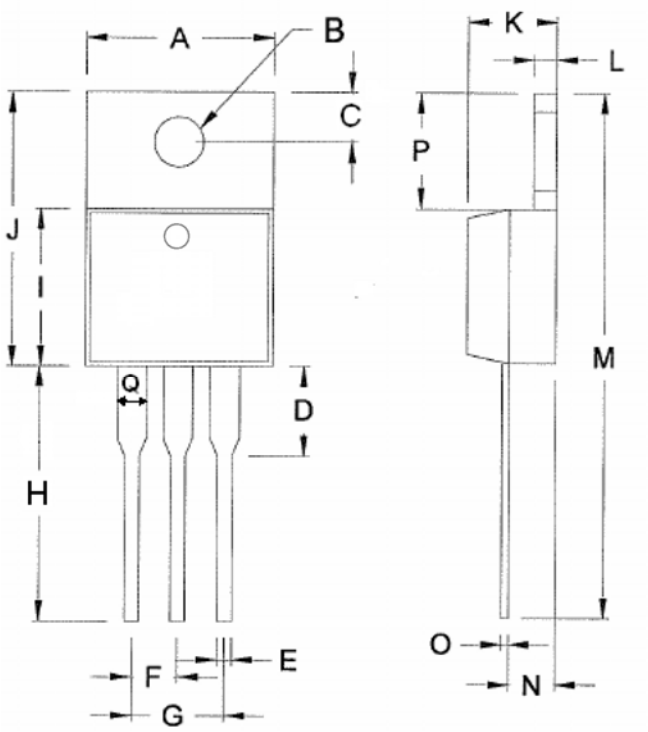
AP12SN60AH-XXJ0
TO-220

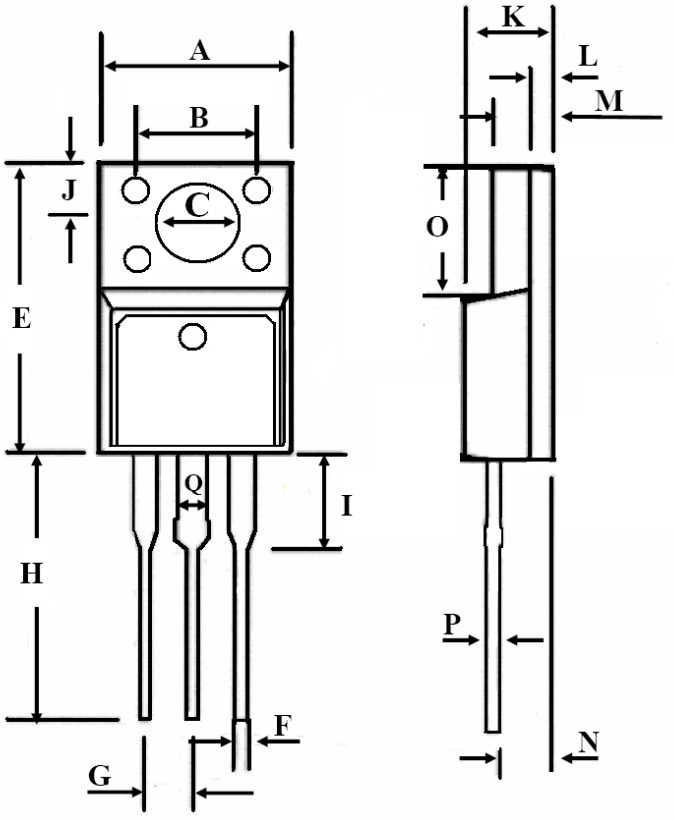
TO-220 DIMENSION			
DIM	MILLIMETERS		
	MIN	MAX	TYP.
A	10.01	10.31	10.16
B	3.66	3.94	3.80
C	2.59	2.89	2.74
D	3.5	3.96	3.73
E	0.70	0.90	0.80
F	2.54 TYP.		
G	4.98	5.18	5.08
H	13.4	13.8	13.6
I	8.5	8.9	8.70
J	14.65	15.35	15.05
K	4.47	4.67	4.57
L	1.22	1.42	1.32
M	28.05	29.15	28.60
N	2.52	2.82	2.67
O	0.31	0.53	0.42
P	6.10	6.50	6.30
Q	1.17	1.37	1.27



600V/12A N-Channel MOSFET

APQ12SN60AF-XXM0
TO-220F

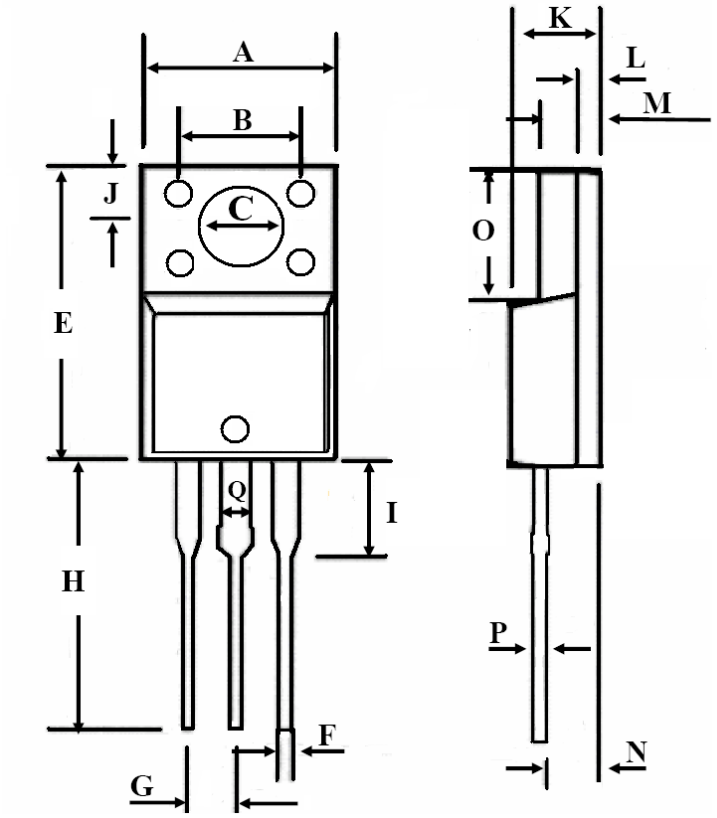
TO-220F DIMENSION			
DIM	MILLIMETERS		
	MIN	MAX	TYP.
A	9.96	10.36	10.16
B	6.50 TYP.		6.50
C	3.00	3.20	3.10
E	15.10	16.07	15.59
F	0.55	1.39	0.97
G	2.54 TYP.		
H	12.37	13.5	12.94
I	2.23	3.90	3.07
J	2.90	3.50	3.2
K	4.45	4.93	4.69
L	1.15 TYP.		
M	2.34	2.74	2.54
N	2.56	2.96	2.76
O	6.50	7.10	6.8
P	0.36	0.68	0.52
Q	1.15	1.66	1.41



600V/12A N-Channel MOSFET

APQ12SN60AF-XXJ0
TO-220F

TO-220F DIMENSION			
DIM	MILLIMETERS		
	MIN	MAX	TYP.
A	9.96	10.36	10.16
B	6.50TYP.		
C	3.5 REF.		
E	14.8	15.2	15.0
F	0.45	0.75	0.55
G	2.54 TYP.		
H	13.23	14.33	13.78
I	3.60	4.00	3.80
J	2.70 TYP.		2.70
K	4.30	4.70	4.50
L	1.30 TYP.		
M	2.80	3.20	3.00
N	2.50	2.90	2.70
O	6.50	7.10	6.8
P	0.45	0.75	0.55
Q	1.05	1.75	1.40



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Note

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